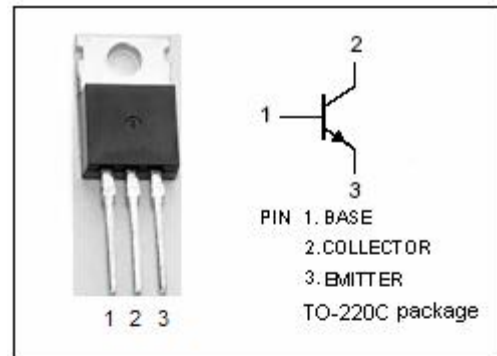


**isc Silicon NPN Power Transistor**
**2SC4230**
**DESCRIPTION**

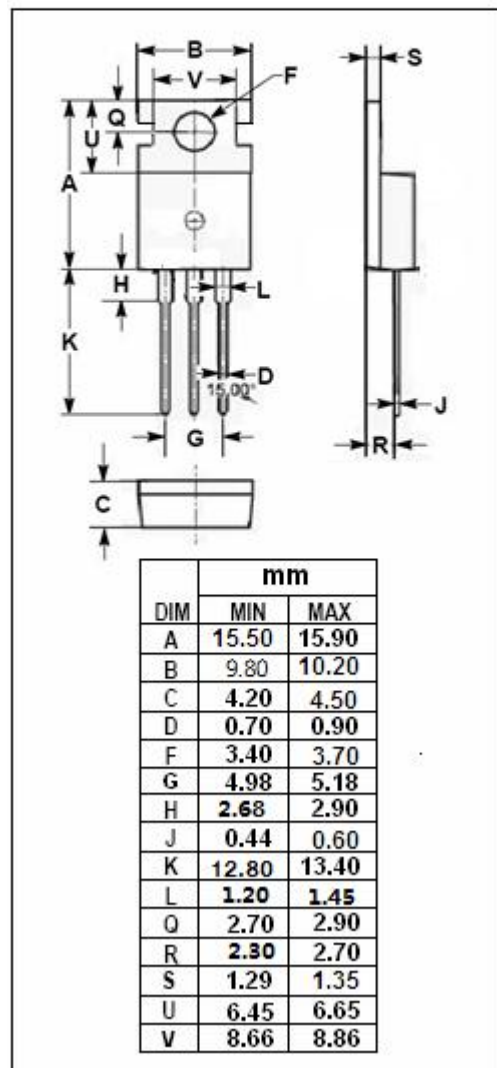
- Collector-Emitter Sustaining Voltage-  
:  $V_{CEO(SUS)} = 800V(\text{Min})$
- Fast Switching speed
- Good Linearity of  $h_{FE}$
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

- Electronic ballasts for fluorescent lighting
- Switch mode power supplies


**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	1200	V
$V_{CEO}$	Collector-Emitter Voltage	800	V
$V_{EBO}$	Emitter-Base Voltage	7	V
$I_C$	Collector Current-Continuous	2	A
$I_{CM}$	Collector Current-Peak	4	A
$I_B$	Base Current-Continuous	1	A
$I_{BM}$	Base Current-Peak	2	A
$P_T$	Total Power Dissipation @ $T_C=25^\circ\text{C}$	50	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$


**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	2.5	$^\circ\text{C/W}$

**isc Silicon NPN Power Transistor**
**2SC4230**
**ELECTRICAL CHARACTERISTICS**

 T<sub>C</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEQ(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 0.1A; I <sub>B</sub> = 0	800			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 1A; I <sub>B</sub> = 0.2A			1.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 1A; I <sub>B</sub> = 0.2A			1.5	V
I <sub>CBO</sub>	Collector Cutoff Current	At rated Voltage			100	μ A
I <sub>CEO</sub>	Collector Cutoff Current	At rated Voltage			100	μ A
I <sub>EBO</sub>	Emitter Cutoff Current	At rated Voltage			100	μ A
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 1A ; V <sub>CE</sub> = 5V	8			
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 1mA ; V <sub>CE</sub> = 5V	7			
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.2A ; V <sub>CE</sub> = 10V		8		MHz

## Switching times

t <sub>on</sub>	Turn-on Time	I <sub>C</sub> = 1A , I <sub>B1</sub> = 0.2A; I <sub>B2</sub> = -0.4A R <sub>L</sub> = 250 Ω ; V <sub>BB2</sub> = 4V			0.5	μ s
t <sub>stg</sub>	Storage Time				3.5	μ s
t <sub>f</sub>	Fall Time				0.3	μ s

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